

Silicon NPN Power Transistors

BU508AW

DESCRIPTION

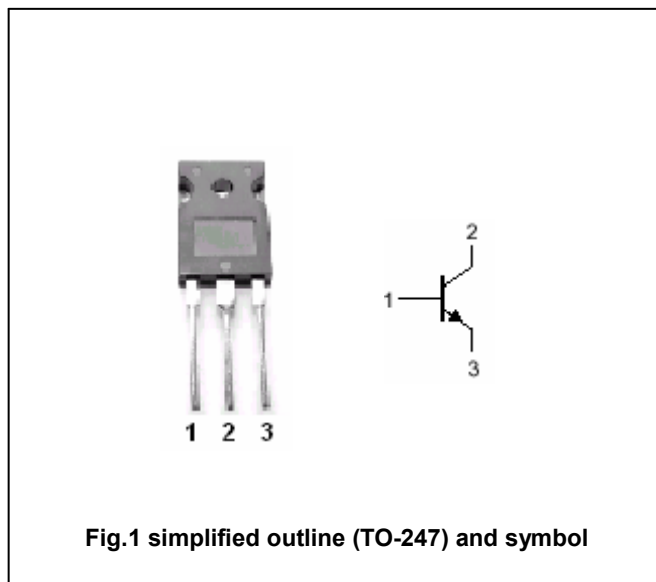
- With TO-247 package
- High voltage
- High speed switching

APPLICATIONS

- For use in horizontal deflection circuits of colour TV receivers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
I_C	Collector current (DC)		8	A
I_{CM}	Collector current -peak		15	A
I_B	Base current (DC)		4	A
I_{BM}	Base current -peak		6	A
P_{tot}	Total power dissipation	$T_C=25^\circ\text{C}$	125	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

Silicon NPN Power Transistors

BU508AW

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0, L=25mH	700			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =1.6A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A ; I _B =2A			1.1	V
I _{CES}	Collector cut-off current	V _{CE} =RatedV _{CE} ; V _{BE} =0 T _C =125°C			1.0 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6.0V; I _C =0			10	mA
h _{FE}	DC current gain	I _C =100mA ; V _{CE} =5V	6	13	30	
f _T	Transition frequency	I _E =0.1A ; V _{CE} =5V		7		MHz
C _{ob}	Output capacitance	V _{CB} =10V; I _E =0; f=1.0MHz		125		pF

Silicon NPN Power Transistors

BU508AW

PACKAGE OUTLINE

